

PD1300-35D32-I InGaAs PIN-PD

PD1300-35D32-I is InGaAs PIN-photodiode featuring excellent responsibility and high photocurrent for near infrared.

◆ Outer dimension (Unit:mm)

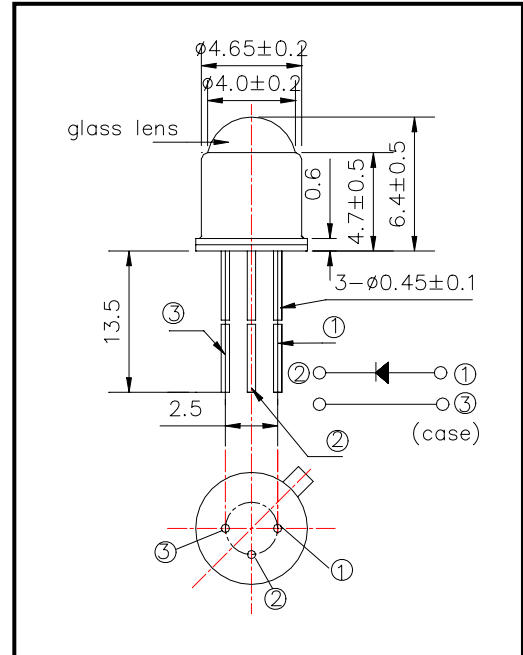
This PIN-photodiode consists of a large chip with 0.35x0.35mm active area mounted on the TO-18 stem and is hermetical sealed by metal can with glass ball lens. These devices are designed to be high photocurrent gains with angle of half sensitivity of ± 15 degrees.

◆ Features

- 1) High Reliability
- 2) High Response

◆ Specifications

- 1) Product Name InGaAs PIN Photo-Diode
- 2) Type No. PD1300-35D32-I
- 3) Chip
 - (1) Active Area 0.35mmx0.35mm
- 4) Package
 - (1) Type TO-18 (3pins)
 - (2) Lens Glass Ball Lens
 - (2) Cap Gold Plated



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	10	V
Operating Temperature	T_{OPR}	-20 ~ +90	$^{\circ}C$
Storage Temperature	T_{STG}	-30 ~ +100	$^{\circ}C$
Soldering Temperature	T_{SOL}	260	$^{\circ}C$

‡Pulse Soldering condition: Soldering condition must be completed within 2 seconds at $240^{\circ}C$

◆ Electro-Optical Characteristics [25 $^{\circ}C$]

Item	Symbol	Condition	Minimum	Typical	Maximum	unit
Photo Responsivity	R_E	$V_R=0V, \lambda_P=1300nm$		0.9		A/W
Photo Current	I_L	$V_R=0V, \lambda_P=1300nm$	22			$\mu A(\pm 1)$
Dark Current	I_D	$V_R=1V$			100	nA
Spectral Responsivity (Peak)	λ_P	$V_R=0V$	1000		1600	nm
Half Angle of Sensitivity	$\theta_{1/2}$	$V_R=0V$		± 15		deg.
Total Capacitance	C_T	$f=1MHz, V_R=1V$		20		pF
Rise/Fall Time(10%~90%)	t_r	$R_L=1K\Omega, V_R=1V$		10		ns
	t_f			5		ns

‡Measured by Epitex's calibrated tool